

TRANSISTOR (NPN)

FEATURES

- Low Collector-Emitter Saturation Voltage
- Large Collector Power Dissipation and Current
- Mini Power Type Package

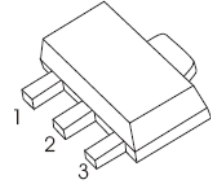
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MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	42	V
V_{CEO}	Collector-Emitter Voltage	22	V
V_{EBO}	Emitter-Base Voltage	7.5	V
I_{CM}	Collector Current	5	A
P_c	Collector Power Dissipation	750	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	167	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER

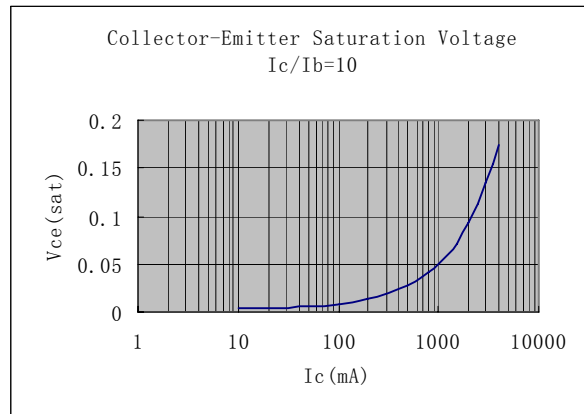
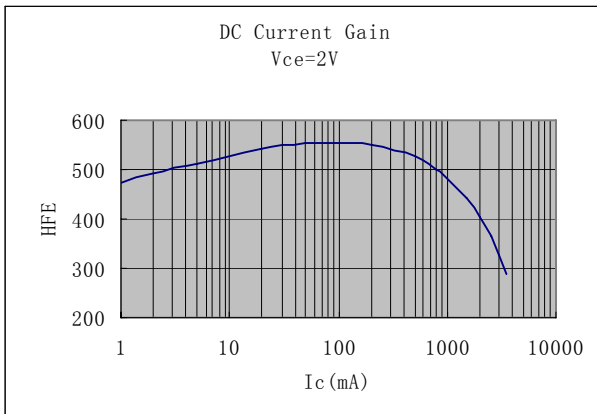


ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

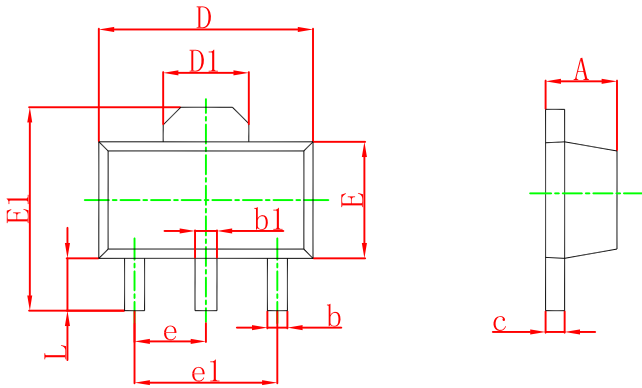
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=10\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=1\text{mA}$		200		
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=500\text{mA}$	340		1000	
	$h_{FE(3)}$	$V_{CE}=2\text{V}, I_C=2\text{A}$	150			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3\text{A}, I_B=0.1\text{A}$			1	V
Transition frequency	f_T	$V_{CE}=6\text{V}, I_C=50\text{mA}, f=200\text{MHz}$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=20\text{V}, I_E=0, f=1\text{MHz}$			50	pF

CLASSIFICATION OF $h_{FE(2)}$

RANK	R	S
RANGE	340 - 600	560 - 1000

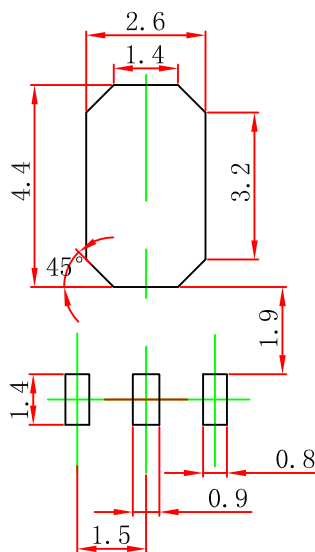


SOT-89 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

SOT-89 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

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